Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-12. (Canceled)

13. (Currently Amended) A device formed by a first body and a second body welded together through a mechanical and electrical connection structure, comprising:

an electrically conductive region welded between said first body and said second body; and

a ~~spacing~~ body region arranged near said electrically conductive region and surrounding an active region.

14. (Original) The device according to claim 13, wherein said electrically conductive region is of a low-melting eutectic material.

15. (Original) The device according to claim 14, wherein said low-melting eutectic material is formed by alternating layers of gold and tin.

16. (Currently Amended) The device according to claim 13, wherein said spacing body ~~region~~ is of dielectric material.

17. (Original) The device according to claim 16, wherein said dielectric material is chosen from among a spun polymer, such as SU8, polyimide, a composite material formed by laminated polymer layers, such as a photosensitive stick foil, and oxynitrides.

18. (Currently Amended) The device according to claim 13, wherein said spacing body ~~region~~ forms a delimiting cavity surrounding said electrically conductive region.

19. (Previously Presented) The device according to claim 13, further comprising a metal region which extends on top of said second body and beneath said electrically conductive region.

20. (Original) The device according to claim 19, wherein said welding region and said metal region are of a material chosen from among titanium, gold and nickel.

21.-26. (Canceled)

27. (Previously Presented) A device comprising:

a first body of semiconductor material;

a first metal region, formed on a first surface of the first body;

a second body of semiconductor material spaced apart from the first body;

a spacer separating the first and second body and in contact with the first surface of the first body and a first surface of the second body, the spacer defining an enclosed space between the first and second bodies;

a second metal region, formed on a first surface of the second body; and

a connection structure bonded to the first and second metal regions, forming thereby an electrical connection between the first and second metal regions.

28. (Original) The device of claim 27 wherein the connection structure is a low-melting eutetic material welded to the first and second metal regions.

29. (Previously Presented) The device of claim 27 wherein, the first and second metal regions and the connection structure are formed within the enclosed space defined by the spacer.

30. (Previously Presented) The device of claim 27 wherein a micromechanical structure is formed within the enclosed space defined by the spacer.

31. (Original) The device of claim 27 wherein the first body of semiconductor material is formed of quartz.

32. (Original) The device of claim 31, further comprising a mirror formed on a second surface of the first body.

33. (Original) The device of claim 31, further comprising a diffractive lens formed on the second surface of the first body.

34. (Previously Presented) The device of claim 13 wherein the device comprises an electromechanical, fluid and optical system.

35. (Previously Presented) The device of claim 13, wherein the active region comprises an electromechanical structure.

36. (Previously Presented) The device of claim 13, wherein the active region comprises an optical structure.

37. (Previously Presented) The device of claim 36, further comprising a mirror formed on a surface of the first body opposite the optical structure.

38. (Currently Amended) The device of claim 36, further comprising:

a third body welded to the first body adjacent to the second body; and

an additional spacing ~~region~~ body formed between the first and third bodies and surrounding an additional active region.

39. (Previously Presented) The device of claim 38, further comprising first and second mirrors formed on opposite faces of the first body.

40. (Previously Presented) The device of claim 13 wherein the first and second bodies are wafers of semiconductor material.

41. (Currently Amended) The device of claim 13 wherein the spacing body ~~region~~ completely surrounds the active region.

42. (Currently Amended) A device formed by a first body and a second body welded together through a mechanical and electrical connection structure, comprising:

an electrically conductive region welded between said first body and said second body; and

a spacing body~~region~~ arranged near said electrically conductive region and surrounding a majority of an active region.

43. (Currently Amended) A device formed by a first body and a second body welded together through a mechanical and electrical connection structure, comprising:

an electrically conductive region welded between said first body and said second body; and

a spacing body ~~region~~ arranged near said electrically conductive region and surrounding more than half of an active region.

44. (Currently Amended) A device formed by a first body and a second body welded together through a mechanical and electrical connection structure, comprising:

an electrically conductive region welded between said first body and said second body; and

a spacing body ~~region~~ arranged near said electrically conductive region and surrounding at least three sides of an active region.

45. (Currently Amended) A device formed by a first body and a second body welded together through a mechanical and electrical connection structure, comprising:

an electrically conductive region welded between said first body and said second body; and

a spacing body ~~region~~ arranged near said electrically conductive region and surrounding at least two contiguous sides of an active region.

46. (New) The device of claim 45, further comprising:

an additional spacing body arranged adjacent to the spacing body such that the spacing body and the additional spacing body delimit, between them, the active region.

47. (New) The device of claim 45, further comprising:

a suspended microstructure positioned in the active region and surrounded by the spacing body.

48. (New) The device of claim 42, further comprising:

a first optical structure formed in the first body; and

a second optical structure formed in the second body and optically aligned with the first optical structure.

49. (New) The device of claim 48 wherein one of the first or second optical structures is a lens.

50. (New) The device of claim 43, further comprising:

a light producing component formed in the first body; and

a mirror formed in the second body and optically aligned with the light producing component.

51. (New) The device of claim 50 wherein the light producing component is a light emitting diode.

52. (New) The device of claim 44 wherein the electrically conductive region is positioned within the active region.

53. (New) A device, comprising:

a first body;

a second body mechanically coupled to the first body; and

means for maintaining a selected distance between the first and second bodies and defining and sealing an active region between the first and second bodies.

54. (New) The device of claim 53 wherein the maintaining, defining, and sealing means comprise a spacer surrounding the active region between the first and second bodies.